

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

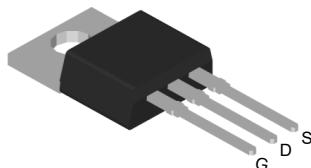
## Product Summary



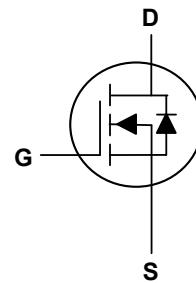
$V_{DS}$	100	V
$I_D$	243	A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	2.2	mΩ

## Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



TO-220 Top View



## Absolute Maximum Ratings( $T_c=25^\circ C$ , unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1</sup>	$I_D @ T_c = 25^\circ C$	243	A
Continuous Drain Current <sup>1</sup>	$I_D @ T_c = 100^\circ C$	172	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	608	A
Single Pulse Avalanche Energy	EAS	500	mJ
Avalanche Current	$I_{AS}$	100	A
Total Power Dissipation	$P_D @ T_c = 25^\circ C$	250	W
Total Power Dissipation	$P_D @ T_c = 100^\circ C$	125	W
Storage Temperature Range	$T_{STG}$	-55 to 175	°C
Operating Junction Temperature Range	$T_J$	-55 to 175	°C

## Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	---	58	°C/W
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	0.6	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	100	---	---	V
Static Drain-Source On-Resistance <sup>2</sup>	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_D=30\text{A}$	---	1.8	2.2	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D = 250\mu\text{A}$	2	---	4	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=80\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	$\text{nA}$
Total Gate Charge	$Q_g$	$V_{\text{DD}}=50\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=30\text{A}$	---	203	---	nC
Gate-Source Charge	$Q_{\text{gs}}$		---	60	---	
Gate-Drain Charge	$Q_{\text{gd}}$		---	53	---	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=50\text{V}$ , $R_G=1\Omega$ , $I_D=1\text{A}$	---	37	---	ns
Rise Time	$T_r$		---	21	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	78	---	
Fall Time	$T_f$		---	107	---	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=50\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	12340	---	pF
Output Capacitance	$C_{\text{oss}}$		---	3995	---	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	37	---	

**Drain-Source Diode Characteristics**

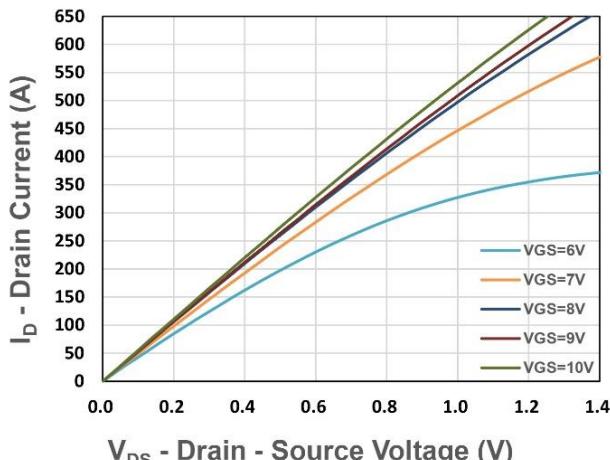
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage <sup>2</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}$ , $I_s=30\text{A}$ , $T_J=25^\circ\text{C}$	---	---	1.1	V
Reverse Recovery Time	$t_{\text{rr}}$	$I_F=10\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$ , $T_J=25^\circ\text{C}$	---	119	---	nS
Reverse Recovery Charge	$Q_{\text{rr}}$		---	347	---	nC

**Note:**

1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

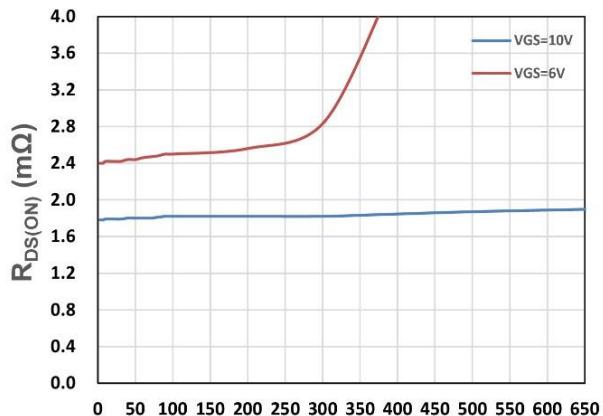
2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$

## Typical Characteristics



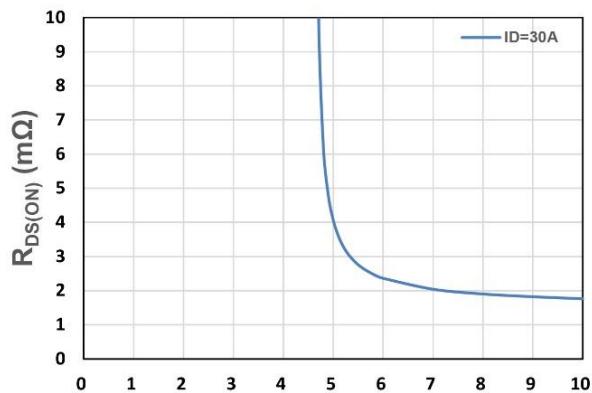
$V_{DS}$  - Drain - Source Voltage (V)

Figure 1. Output Characteristics



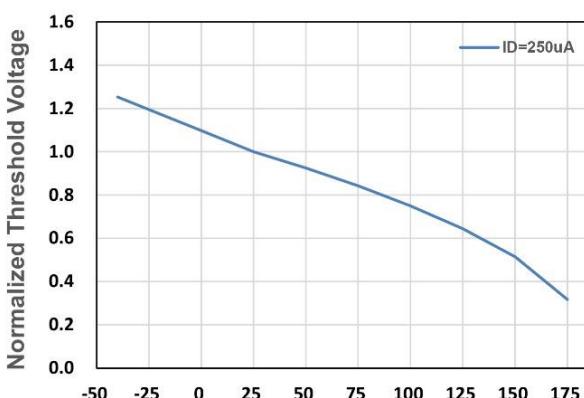
$I_D$  - Drain Current (A)

Figure 2. On-Resistance vs. ID



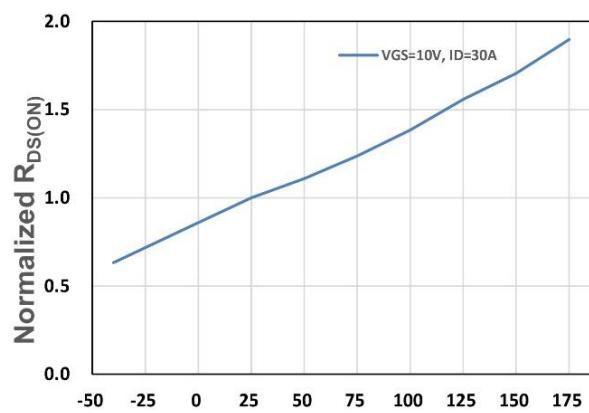
$V_{GS}$  - Gate - Source Voltage (V)

Figure 3. On-Resistance vs. VGS



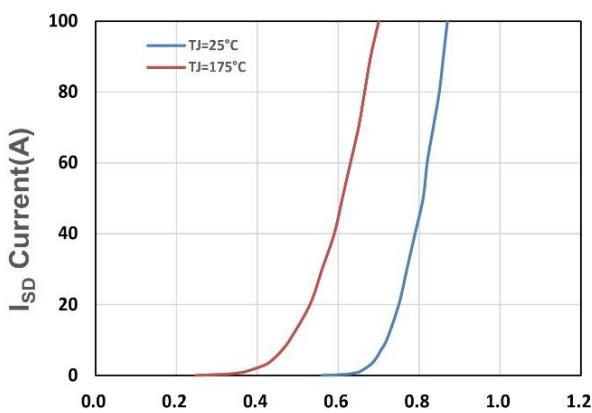
$T_j$ , Junction Temperature(°C)

Figure 4. Gate Threshold Voltage



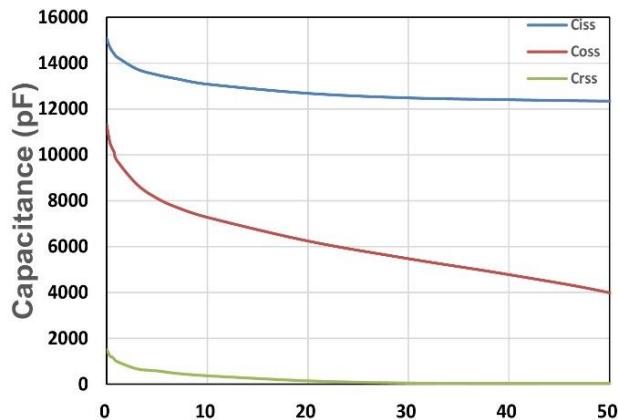
$T_j$  , Junction Temperature(°C)

Figure 5. Drain-Source On Resistance

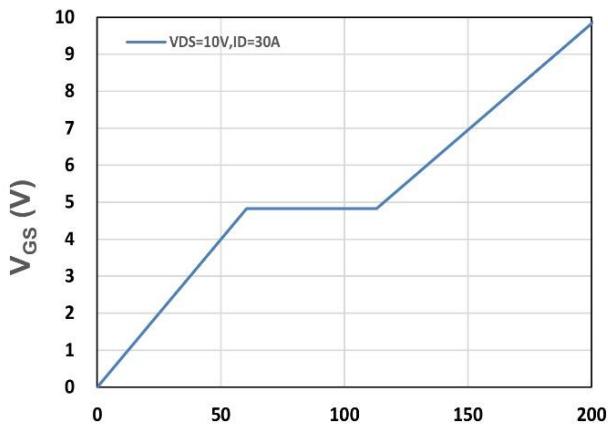


$V_{SD}$ , Source-Drain Voltage(V)

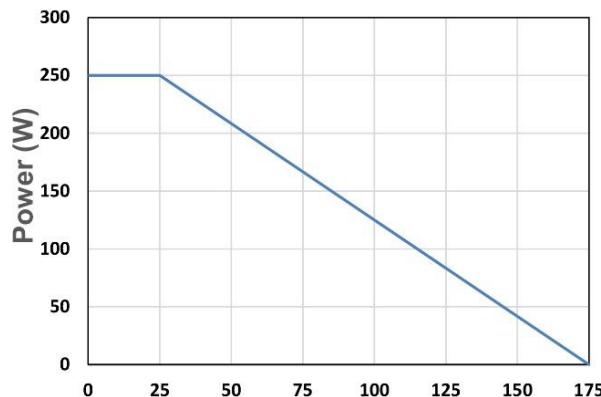
Figure 6. Source-Drain Diode Forward



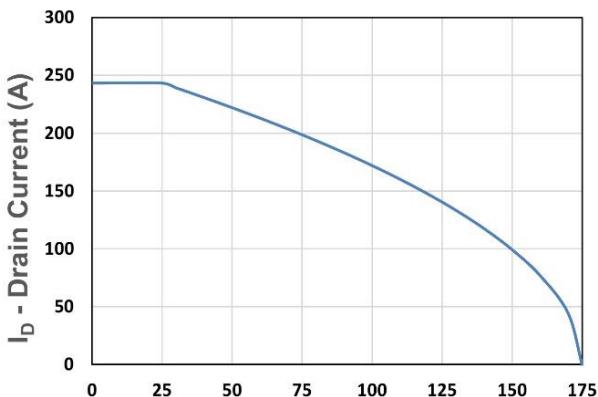
**V<sub>DS</sub>** - Drain - Source Voltage (V)  
Figure 7. Capacitance



**Q<sub>g</sub>, Total Gate Charge (nC)**  
Figure 8. Gate Charge Characteristics



**T<sub>c</sub>** - Case Temperature (°C)  
Figure 9. Power Dissipation



**T<sub>c</sub>** - Case Temperature (°C)  
Figure 10. Drain Current

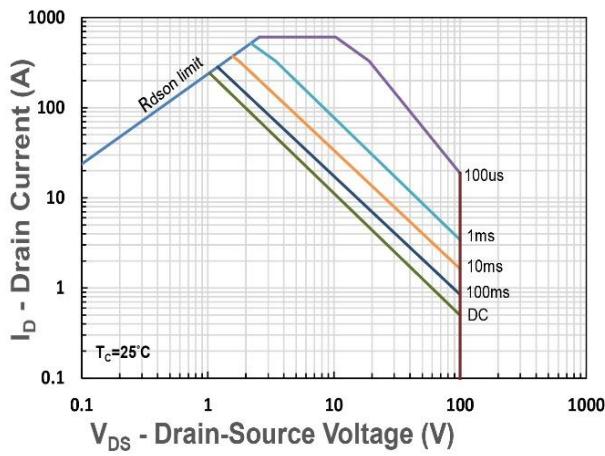


Figure 11. Safe Operating Area

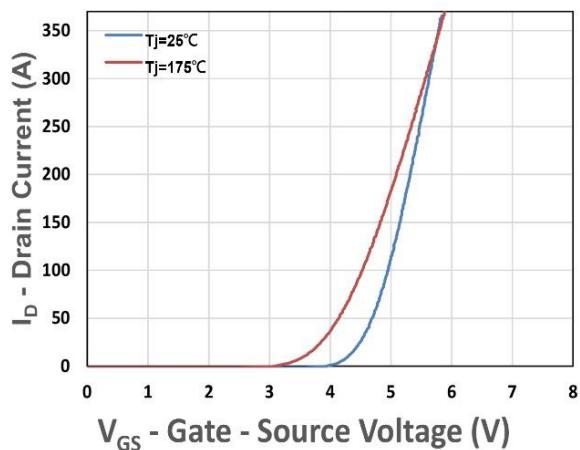
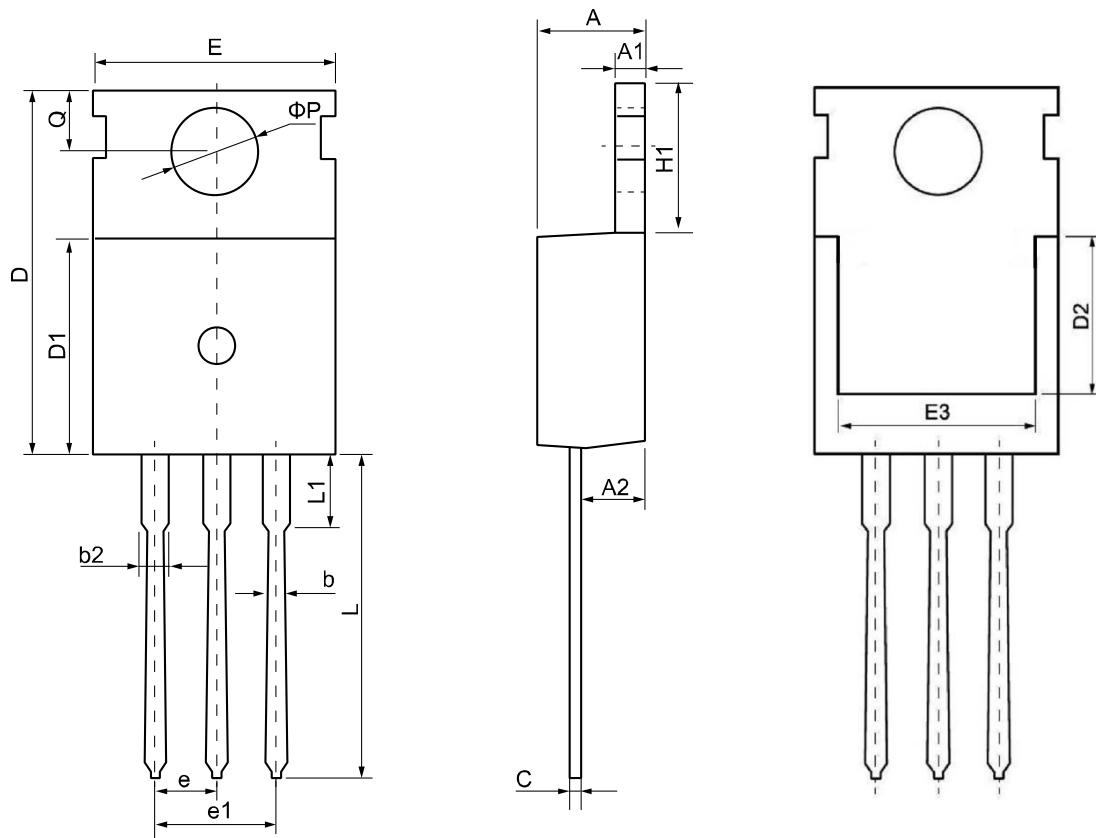


Figure 12. Transfer Characteristics

### TO-220 Package Outline Dimensions



<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	4.30	4.55	4.75	<b>E</b>	9.65	10.00	10.25
<b>A1</b>	1.15	1.30	1.45	<b>E3</b>	7.00	--	--
<b>A2</b>	2.20	2.40	2.60	<b>e</b>	2.54 BSC		
<b>b</b>	0.70	0.80	0.95	<b>e1</b>	5.08 BSC		
<b>b2</b>	1.17	1.27	1.47	<b>H1</b>	6.30	6.50	6.80
<b>c</b>	0.40	0.50	0.65	<b>L</b>	12.70	13.50	14.10
<b>D</b>	15.30	15.60	15.90	<b>L1</b>	--	3.20	3.95
<b>D1</b>	8.90	9.10	9.35	<b>φP</b>	3.40	3.60	3.80
<b>D2</b>	5.50	--	--	<b>Q</b>	2.60	2.80	3.00